

SANYO	No. 4938	STK730-010
	Self-Excitation Type Semi-Regulated Switching Regulator (110W Output)	

Overview

The STK730-010 incorporates on-chip all the power switching, amplifier, error detection and overcurrent protection circuits required in a self-excitation type semi-regulated off-line switching regulator. As a result, it can be used in the design of switching power supplies with minimal number of external components. Furthermore, the adoption of MOSFET power switching elements supports a higher oscillator frequency than that possible with bipolar transistors. This allows smaller pulse transformers and capacitors to be used, making it possible to construct miniature power supply systems.

Applications

- CRT/CTV power supplies
- Office automation equipment power supplies

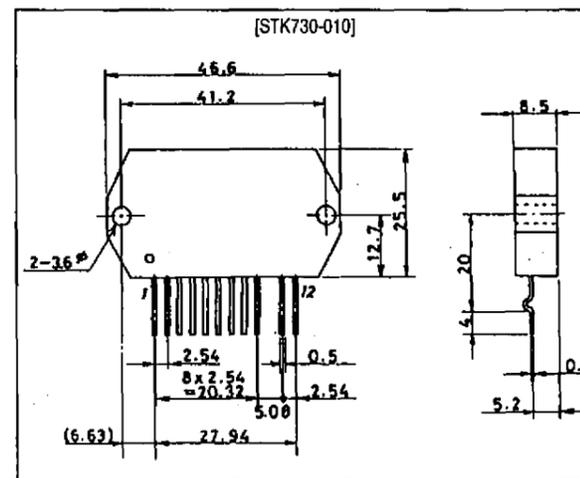
Features

- Power MOSFET devices
- Ideal for semi-regulated control switching supplies
- Error detection circuit on-chip ($40.5 \pm 0.5V$ set reference voltage)
- Overcurrent protection circuit on-chip
- Pin compatible with all other devices in the same series of devices with 110 to 280W power ratings
- Higher oscillator frequency allows the use of smaller pulse transformers
- IMST substrate acts as an electromagnetic shield, making low-noise designs possible

Package Dimensions

unit: mm

4121



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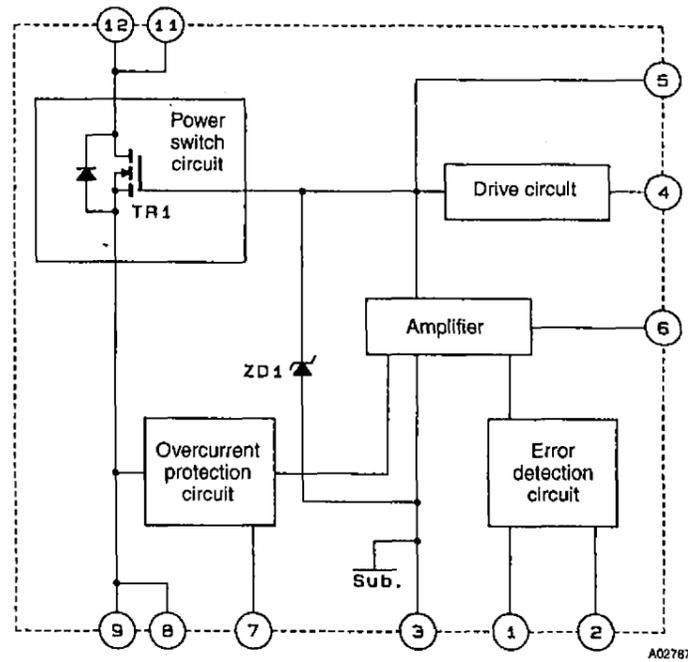
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Block Diagram



The back surface of the IC is not an insulator, and is effectively at pin 3 potential.

Pin Functions

Number	Function
1	V_{ref} (40.5V typ) input
2	Error detection level
3	Ground
4	Drive voltage input
5	TR1 gate
6	Amplifier circuit control
7	OCP setting level input
8	TR1 source
9	
11	TR1 drain
12	

Specifications

Maximum Ratings at $T_a = 25^\circ\text{C}$, $T_c = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Operating substrate temperature	$T_c \text{ max}$	Recommended value is 105°C .	115	$^\circ\text{C}$
AC input voltage	V_{AC}	Specified test circuit	140	Vrms
Operating temperature	T_{opr}		-10 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}		-30 to +115	$^\circ\text{C}$
Maximum output power	$W_o \text{ max}$	Specified test circuit, $V_o = 135\text{V}$	110	W

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Parameter	Symbol	Conditions	Ratings	Unit
[TR1]				
Drain current	I_D	Refer to ASO characteristics for overcurrent condition.	6	A
Pulse drain current	$I_{D(pulse)}$		20	A
Drain reverse current	I_{DR}		6	A
Gate-source voltage	V_{GS}		± 30	V
Allowable power dissipation	P_D		78.1	W
Chip junction temperature	$T_j \text{ max}$		150	$^{\circ}\text{C}$
Thermal resistance	$\theta_j\text{-c}$		1.6	$^{\circ}\text{C/W}$
[ZD1]				
Allowable power dissipation	P_{ZD1}		500	mW
Chip junction temperature	$T_j(\text{ZD1}) \text{ max}$		125	$^{\circ}\text{C}$
Thermal resistance	$\theta_j\text{-c}(\text{ZD1})$		0.2	$^{\circ}\text{C/mW}$

Allowable Operating Ranges at $T_a = 25^{\circ}\text{C}$

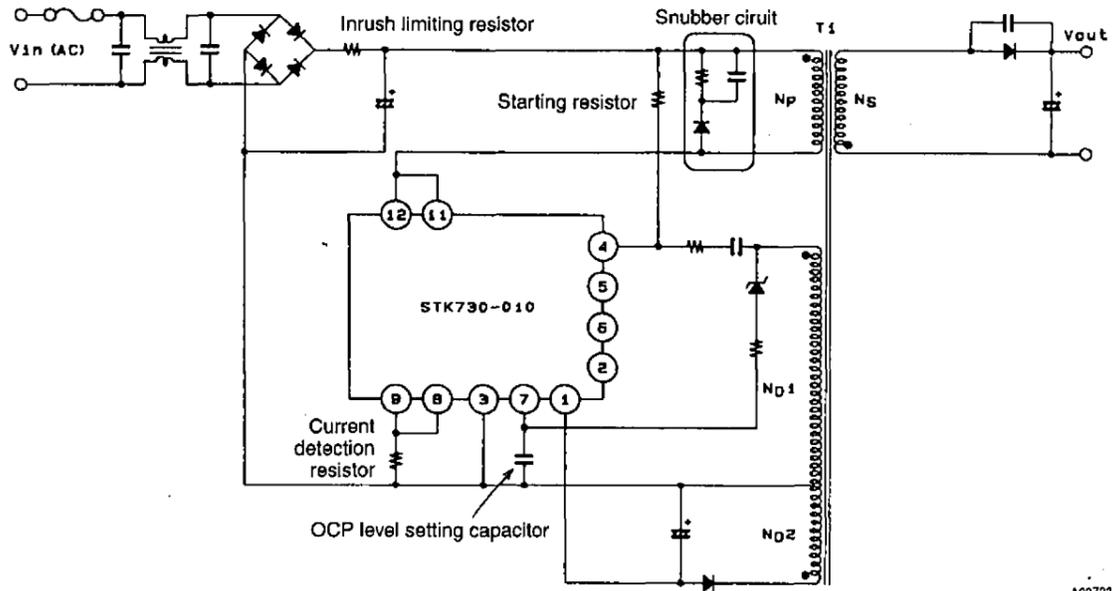
Parameter	Symbol	Conditions	Ratings	Unit
Pin 4 input voltage	V_4		± 8 to ± 24	V
Oscillator frequency	f_{osc}		20 to 120	kHz

Operating Characteristics at $T_a = 25^{\circ}\text{C}$, $T_c = 25^{\circ}\text{C}$ unless otherwise specified, specified test circuit

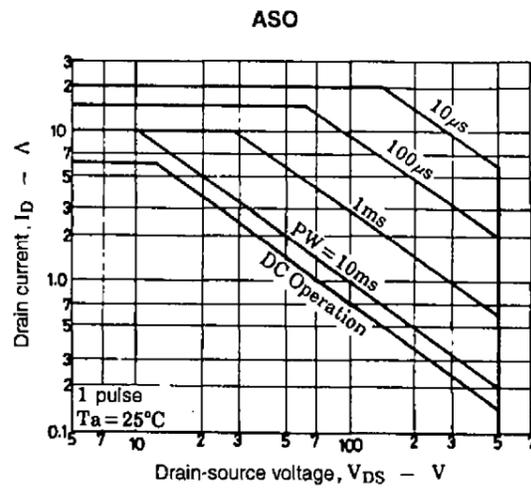
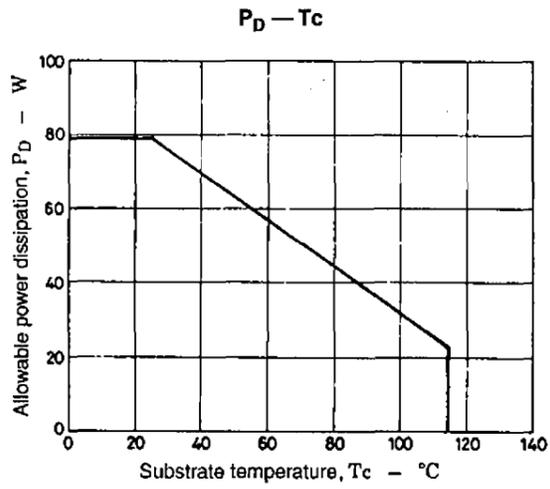
Parameter	Symbol	Conditions	min	typ	max	Unit
Output voltage setting		$I_N = 8\text{mA}$	40.0	40.5	41.0	V
Output voltage temperature coefficient		$T_c = 0$ to 105°C , $I_N = 8\text{mA}$	-	7	-	$\text{mV}/^{\circ}\text{C}$
[TR1]						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{mA}$, $V_{GS} = 0\text{V}$	500	-	-	V
Gate-source cutoff voltage	$V_{GS(off)}$	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	-	3.0	V
ON resistance	$R_{DS(on)}$	$I_D = 2.5\text{A}$, $V_{GS} = 10\text{V}$	-	1.4	1.8	Ω
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	800	-	pF
[ZD1]						
Zener voltage	V_Z	$I_Z = 5\text{mA}$	23.7	-	26.3	V

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Circuit Function Diagram

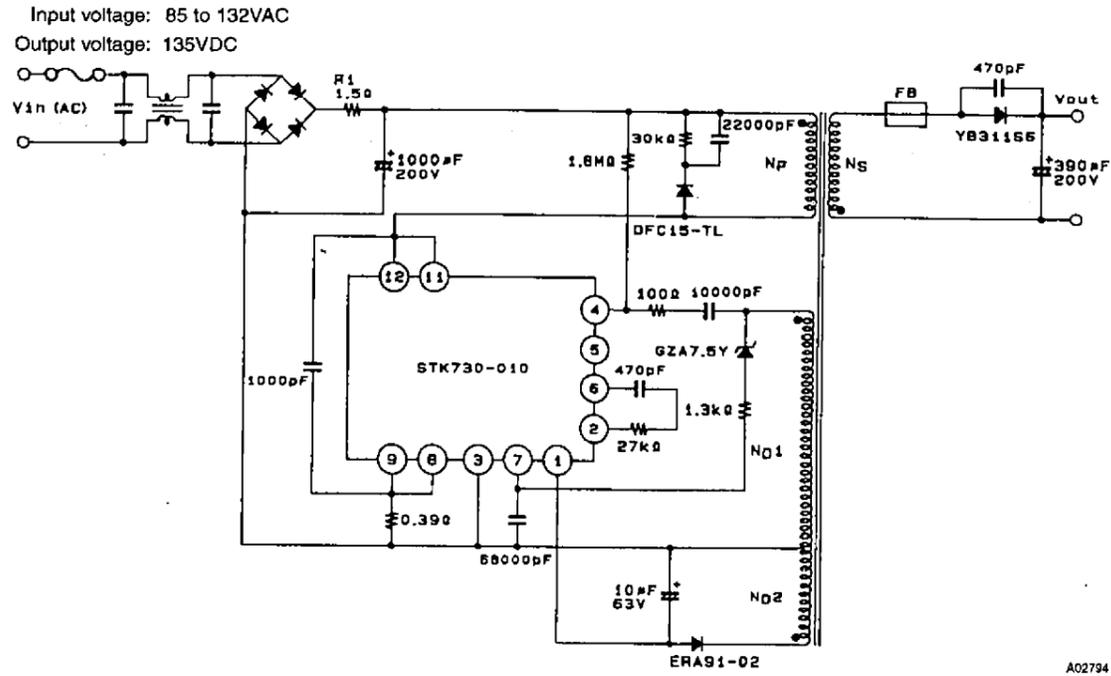


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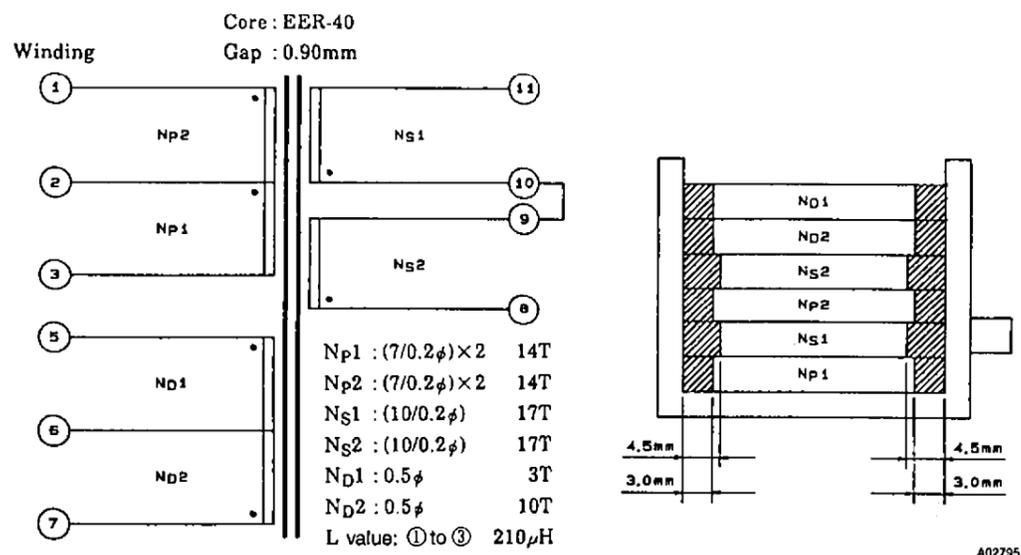


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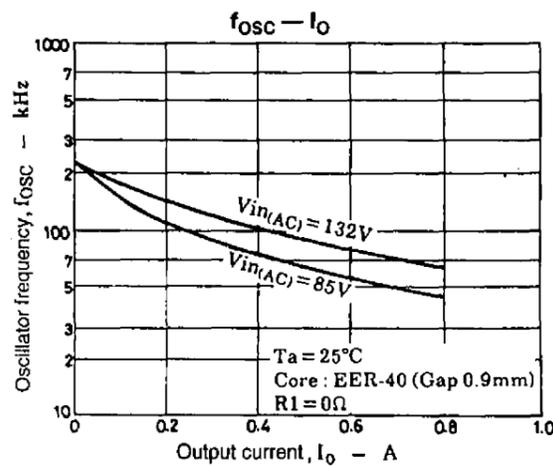
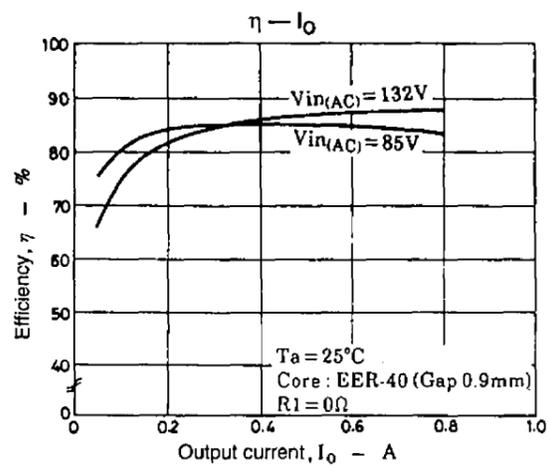
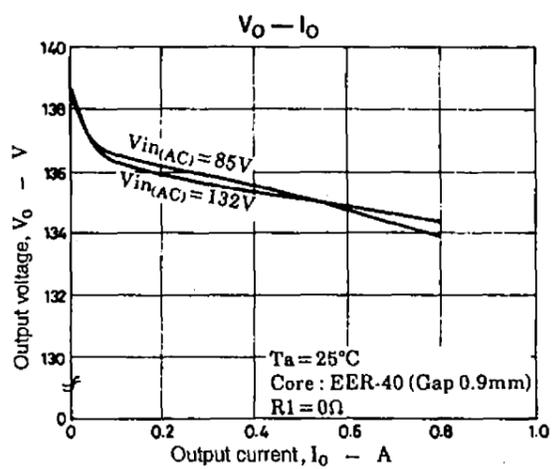
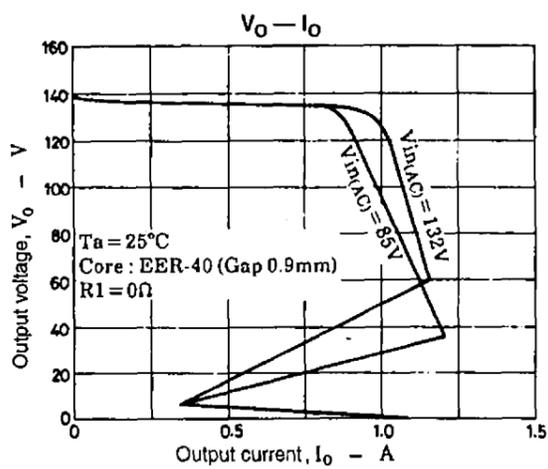
Sample Application Circuit



Pulse Transformer Specifications



STK730-010



Series Organization

These devices form a series with varying output power ratings.

Device	Maximum ratings				Operating characteristics			
	V _{DSS} [V]	T _{stg} [°C]	T _c max [°C]	T _j max [°C]	I _o [A]	Input voltage [V]	Output power [W]	ON resistance [Ω]
STK730-010	500	-30 to +115	+115	+150	6.0	85 to 132	110	1.4
STK730-020					8.0		145	0.8
STK730-030					10.0		180	0.7
STK730-040					12.0		210	0.55
STK730-050					15.0		280	0.3
STK730-060	900	-30 to +115	+115	+150	3.0	170 to 264	110	5.0
STK730-070					5.0		180	3.0
STK730-080					6.0		210	2.0
STK730-090					8.0		280	1.2